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DLS 048

TO-3
CASE

30 Amp Center Tapped Silicon Integrated Rectifiers

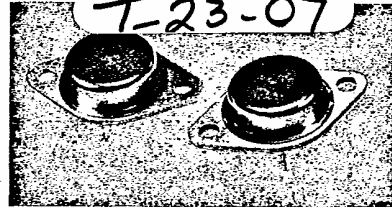
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Controlled Avalanche Types with 250V,
450V, and 650V Minimum Avalanche Ratings

Non-Controlled Avalanche Types with
100V, 200V, 400V and 600V V_{RRM} Ratings

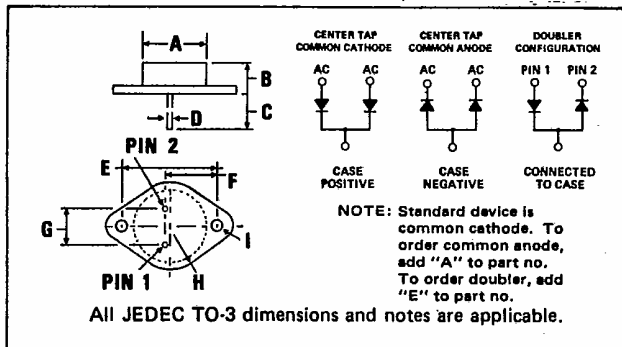
250 Amps Peak One Half Cycle Surge Current

Fast Recovery Types with 200 Nanosecond Maximum t_{rr}



MAXIMUM RATING AT $T_A = 25^\circ\text{C}$ (unless otherwise specified)	SYMBOL	CONTROLLED AVALANCHE			NON-CONTROLLED AVALANCHE				FAST RECOVERY TIME				UNITS
		R702	R704	R706	R711	R712	R714	R716	R711X	R712X	R714X	R716X	
Series Number													
DC Blocking Voltage	V_{RM}	200	400	600	100	200	400	600	100	200	400	600	Volts
Working Peak Reverse Voltage	V_{RWM}												
Peak Repetitive Reverse Voltage	V_{RRM}												
RMS Reverse Voltage	$V_{R(RMS)}$	140	280	420	70	140	280	420	70	140	280	420	Volts
Power Dissipation in V_{BR} Region for 100 μ sec Square Wave (Per diode)	P_{RM}	1500			NA				NA				Watts
Continuous Power Dissipation in V_{BR} Region at $T_C = 100^\circ\text{C}$ (Per diode)	P_R	4			NA				NA				Watts
Peak Surge Current, $\frac{1}{2}$ Cycle at 60 Hz, (Non-Rep) and $T_C = 100^\circ\text{C}$ (Per diode) (Fig. 2)	I_{FSM}				300				150				Amps
Peak Surge Current, 1 sec at 60 Hz and $T_C = 100^\circ\text{C}$ (Per diode) (Fig. 2)	I_{FRM}				60				50				Amps
Avg. Forward Current at $T_C = 100^\circ\text{C}$ (Per diode)	I_o				15								Amps
Junction Operating and Storage Temperature Range	T_J, T_{STG}				-65 to +150								$^\circ\text{C}$
Fusing Data	I^2T				375				95				Amp ² Sec.

ELECTRICAL CHARACTERISTICS AT $T_A = 25^\circ\text{C}$ (unless otherwise specified)	SYMBOL	CONTROLLED AVALANCHE			NON-CONTROLLED AVALANCHE				FAST RECOVERY TIME				UNITS
		R702	R704	R706	R711	R712	R714	R716	R711X	R712X	R714X	R716X	
Series Number													
Minimum Avalanche Voltage	V_{BR}	250	450	650	NA				NA				Volts
Maximum Avalanche Voltage	V_{BR}	700	900	1100	NA				NA				Volts
Maximum Instantaneous Forward Voltage Drop (Per diode) at 15 Amps (Fig. 3)	V_{FM}				1.2				1.4				Volts
Maximum Reverse Current at Rated V_{RM} at $T_C = 100^\circ\text{C}$	I_{RM}				1				5				mA
Maximum Reverse Recovery Time at $I_F = 1\text{A}, I_R = 2\text{A}$ (Fig. 5)	t_{rr}				NA				200				nsec
Maximum Thermal Resistance, Junction to Case	$R_{\theta J-C}$				1.5								$^\circ\text{C/W}$



LTR	INCHES	MILLIMETERS
A	.77 Dia.	19,56
B	.323-.342	8,20-8,69
C	.40 Min.	10,16
D	.038-.043 Dia.	.97-1,09
E	1,180-1,194	29,97-30,33
F	.665-.675	16,89-17,15
G	.426-.440	10,82-11,18
H	.525R max.	13,34
I	.151-.161 Dia.	3,34-4,09

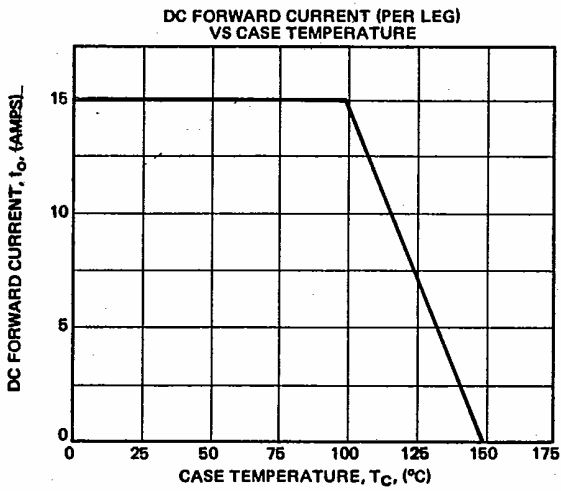


FIGURE 1

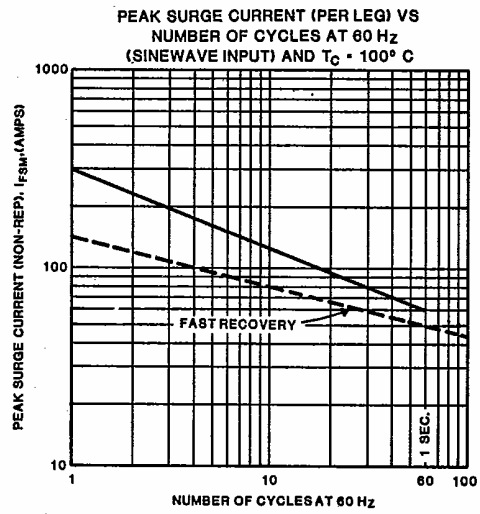


FIGURE 2

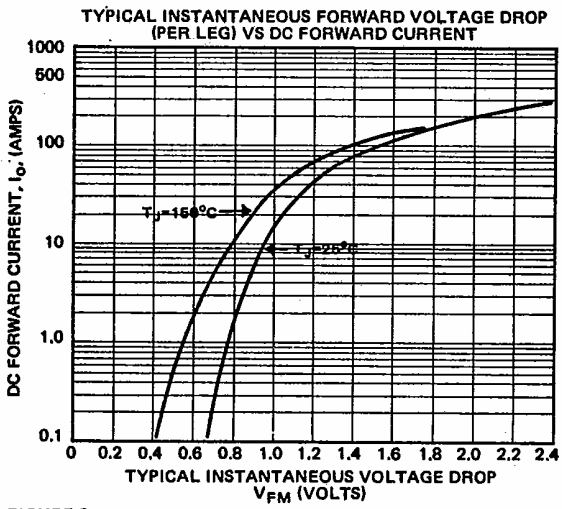


FIGURE 3

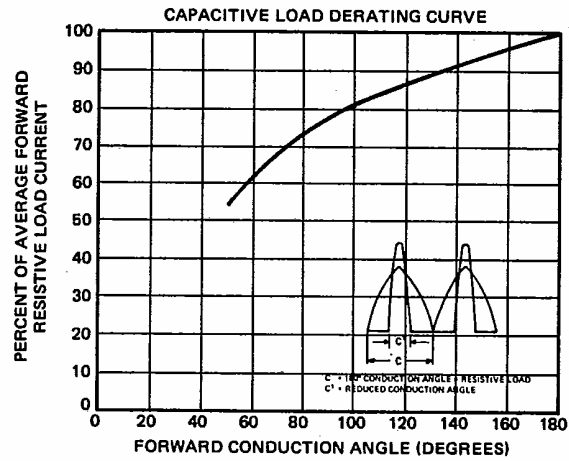


FIGURE 4

